International Rectifier

PD - 9.783A

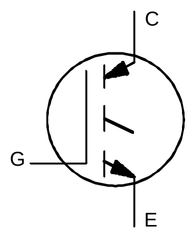
IRGB430U

INSULATED GATE BIPOLAR TRANSISTOR

UltraFast IGBT

Features

- Switching-loss rating includes all "tail" losses
- Optimized for high operating frequency (over 5kHz) See Fig. 1 for Current vs. Frequency curve



n-channel

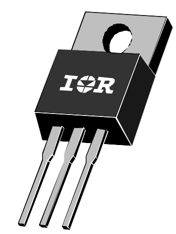
V_{CES} = 500V

$V_{CE(sat)} \leq 3.0V$

@V_{GE} = 15V, I_C = 15A

Description

Insulated Gate Bipolar Transistors (IGBTs) from International Rectifier have higher usable current densities than comparable bipolar transistors, while at the same time having simpler gate-drive requirements of the familiar power MOSFET. They provide substantial benefits to a host of high-voltage, high-current applications.



TO-220AB

Absolute Maximum Ratings

	Parameter	Max.	Units
V_{CES}	Collector-to-Emitter Voltage	500	V
I_C @ T_C = 25°C	Continuous Collector Current	25	A
I_C @ T_C = 100°C	Continuous Collector Current	15	
I_{CM}	Pulsed Collector Current ①	50	
I_{LM}	Clamped Inductive Load Current ②	50	
V_{GE}	Gate-to-Emitter Voltage	±20	V
E_{ARV}	Reverse Voltage Avalanche Energy ③	10	mJ
P_D @ T_C = 25°C	Maximum Power Dissipation	100	W
P_D @ T_C = 100°C	Maximum Power Dissipation	42	
T_J T_{STG}	Operating Junction and Storage Temperature Range	-55 to +150	°C
	Soldering Temperature, for 10 sec.	300 (0.063 in. (1.6mm) from case)	
	Mounting torque, 6-32 or M3 screw.	10 lbf•in (1.1N•m)	

Thermal Resistance

	Parameter	Min.	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case	—	—	1.2	°C/W
$R_{\theta CS}$	Case-to-Sink, flat, greased surface	—	0.50	—	
$R_{\theta JA}$	Junction-to-Ambient, typical socket mount	—	—	80	
Wt	Weight	—	2.0 (0.07)	—	g (oz)

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Electrical Characteristics @ T_J = 25°C (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)CES}$	Collector-to-Emitter Breakdown Voltage	500	—	—	V	V_{GE} = 0V, I_C = 250µA
$V_{(BR)ECS}$	Emitter-to-Collector Breakdown Voltage ④	20	—	—	V	V_{GE} = 0V, I_C = 1.0A
$\Delta V_{(BR)CES}/\Delta T_J$	Temperature Coeff. of Breakdown Voltage	—	0.46	—	V/°C	V_{GE} = 0V, I_C = 1.0mA
$V_{CE(on)}$	Collector-to-Emitter Saturation Voltage	—	2.3	3.0	V	I_C = 15A, V_{GE} = 15V
		—	2.8	—		I_C = 25A, See Fig. 2, 5
		—	2.6	—		I_C = 15A, T_J = 150°C
$V_{GE(th)}$	Gate Threshold Voltage	3.0	—	5.5		V_{CE} = V_{GE}, I_C = 250µA
$\Delta V_{GE(th)}/\Delta T_J$	Temperature Coeff. of Threshold Voltage	—	-11	—	mV/°C	V_{CE} = V_{GE}, I_C = 250µA
g_{fe}	Forward Transconductance ⑤	2.3	8.1	—	S	V_{CE} = 100V, I_C = 15A
I_{CES}	Zero Gate Voltage Collector Current	—	—	250	µA	V_{GE} = 0V, V_{CE} = 500V
		—	—	1000		V_{GE} = 0V, V_{CE} = 500V, T_J = 150°C
I_{GES}	Gate-to-Emitter Leakage Current	—	—	±100	nA	V_{GE} = ±20V

Switching Characteristics @ T_J = 25°C (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
Q_g	Total Gate Charge (turn-on)	—	31	47	nC	I_C = 15A
Q_{ge}	Gate - Emitter Charge (turn-on)	—	6.2	9.3		V_{CC} = 400V See Fig. 8
Q_{gc}	Gate - Collector Charge (turn-on)	—	12	19		V_{GE} = 15V
$t_{d(on)}$	Turn-On Delay Time	—	29	—	ns	T_J = 25°C
t_r	Rise Time	—	11	—		I_C = 15A, V_{CC} = 400V
$t_{d(off)}$	Turn-Off Delay Time	—	91	160		V_{GE} = 15V, R_G = 23Ω
t_f	Fall Time	—	66	120		Energy losses include "tail"
E_{on}	Turn-On Switching Loss	—	0.24	—	mJ	
E_{off}	Turn-Off Switching Loss	—	0.17	—		See Fig. 9, 10, 11, 14
E_{ts}	Total Switching Loss	—	0.41	0.61		
$t_{d(on)}$	Turn-On Delay Time	—	13	—	ns	T_J = 150°C,
t_r	Rise Time	—	27	—		I_C = 15A, V_{CC} = 400V
$t_{d(off)}$	Turn-Off Delay Time	—	130	—		V_{GE} = 15V, R_G = 23Ω
t_f	Fall Time	—	130	—		Energy losses include "tail"
E_{ts}	Total Switching Loss	—	0.76	—	mJ	See Fig. 10, 14
L_E	Internal Emitter Inductance	—	7.5	—	nH	Measured 5mm from package
C_{ies}	Input Capacitance	—	660	—	pF	V_{GE} = 0V
C_{oes}	Output Capacitance	—	110	—		V_{CC} = 30V See Fig. 7
C_{res}	Reverse Transfer Capacitance	—	12	—		f = 1.0MHz

Notes:

① Repetitive rating; V_{GE}=20V, pulse width limited by max. junction temperature. (See fig. 13b)

② V_{CC}=80%(V_{CES}), V_{GE}=20V, L=10µH, R_G= 23Ω, (See fig. 13a)

③ Repetitive rating; pulse width limited by maximum junction temperature.

④ Pulse width ≤ 80µs; duty factor ≤ 0.1%.

⑤ Pulse width 5.0µs, single shot.

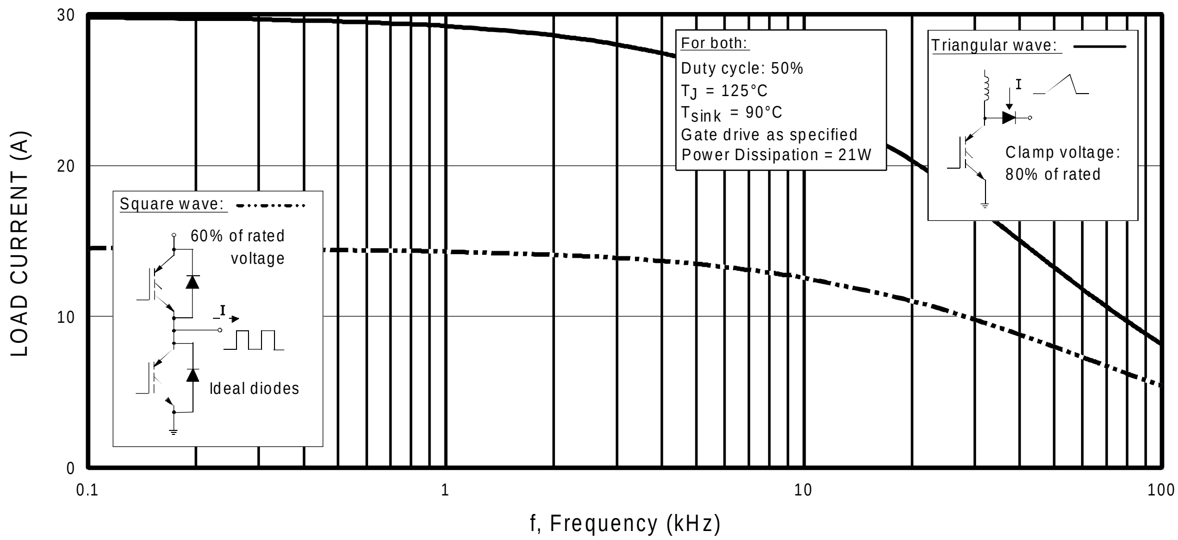

Fig. 1 - Typical Load Current vs. Frequency
(For square wave, $I=I_{RMS}$ of fundamental; for triangular wave, $I=I_{PK}$)

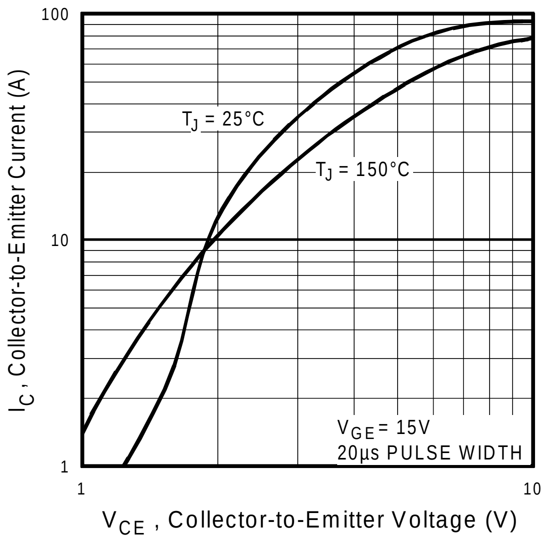

Fig. 2 - Typical Output Characteristics

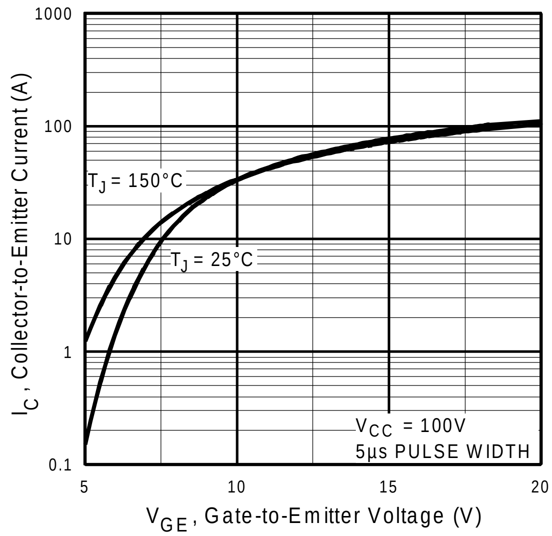

Fig. 3 - Typical Transfer Characteristics

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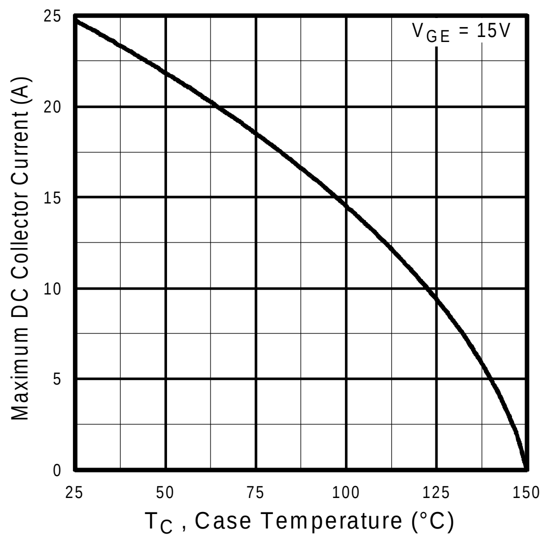

Fig. 4 - Maximum Collector Current vs. Case Temperature

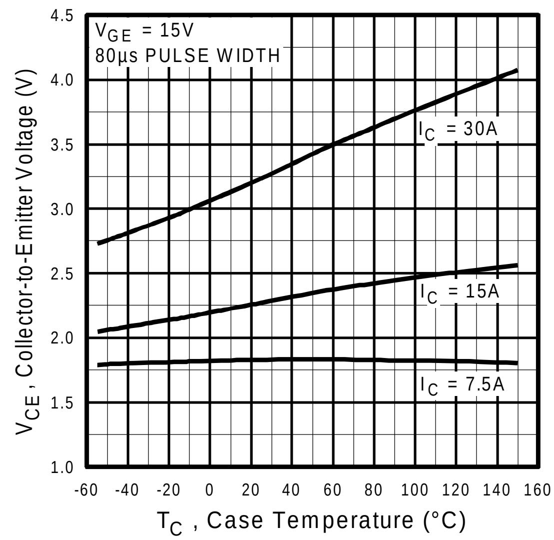

Fig. 5 - Collector-to-Emitter Voltage vs. Case Temperature

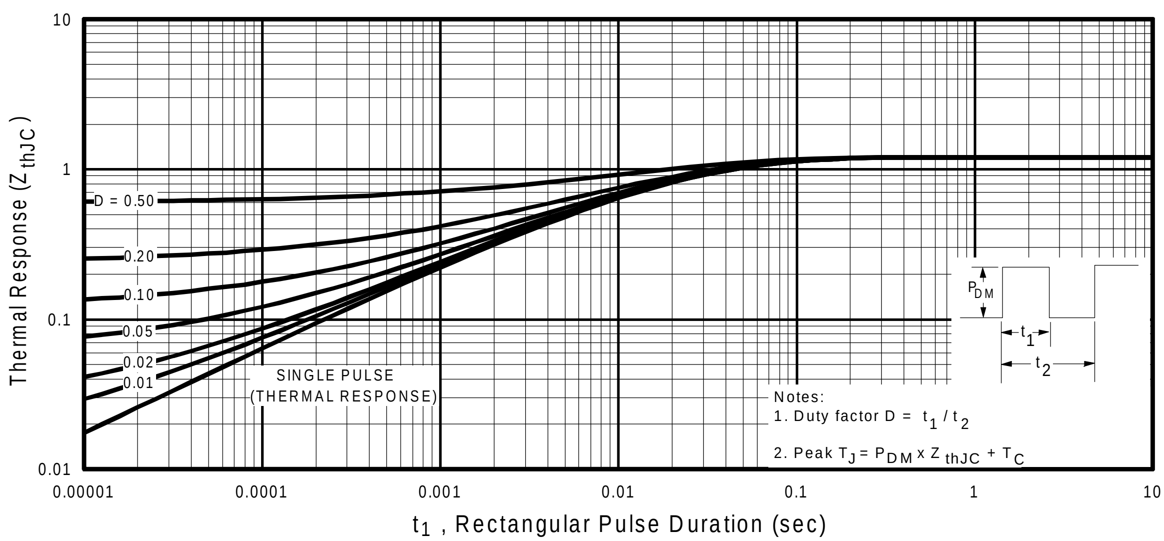

Fig. 6 - Maximum Effective Transient Thermal Impedance, Junction-to-Case

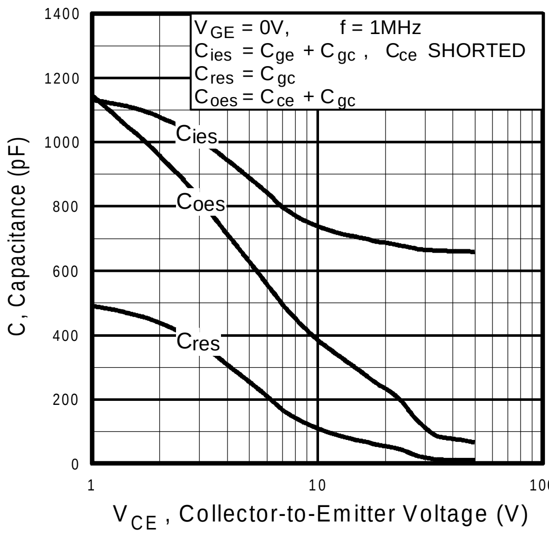

Fig. 7 - Typical Capacitance vs. Collector-to-Emitter Voltage

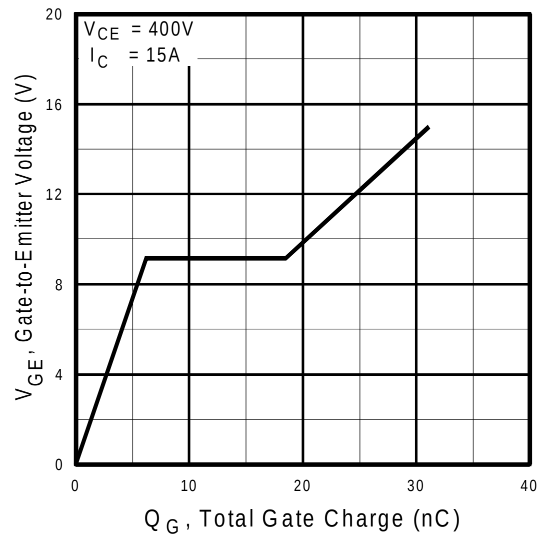

Fig. 8 - Typical Gate Charge vs. Gate-to-Emitter Voltage

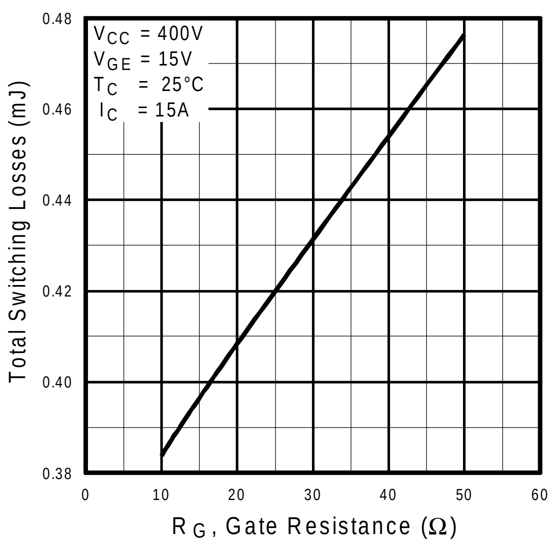

Fig. 9 - Typical Switching Losses vs. Gate Resistance

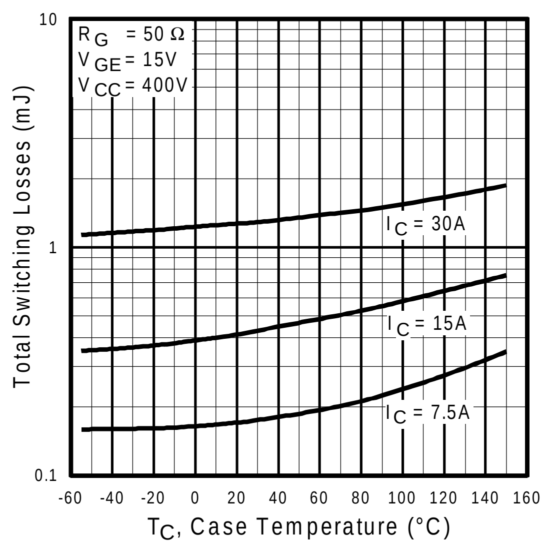

Fig. 10 - Typical Switching Losses vs. Case Temperature

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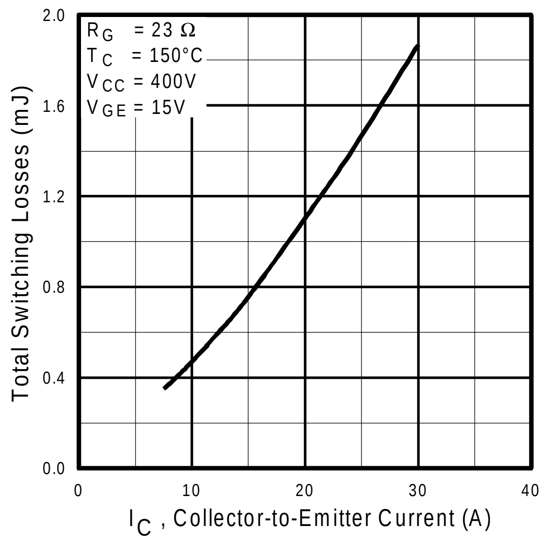

Fig. 11 - Typical Switching Losses vs. Collector-to-Emitter Current

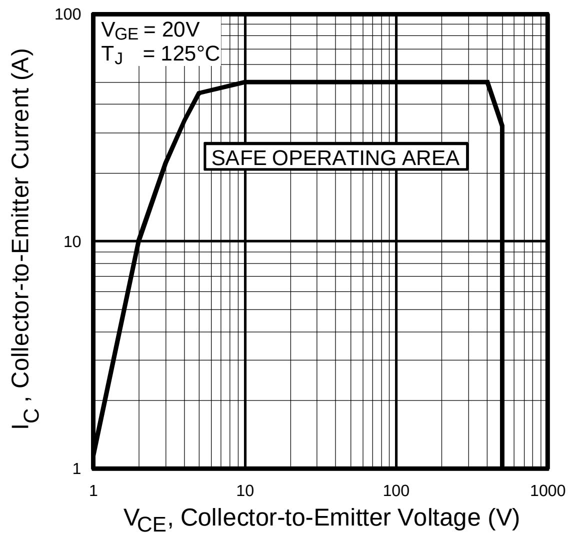

Fig. 12 - Turn-Off SOA

Refer to Section D for the following:

Appendix A: Section D - page D-3

Fig. 13a - Clamped Inductive Load Test Circuit
Fig. 13b - Pulsed Collector Current Test Circuit
Fig. 14a - Switching Loss Test Circuit
Fig. 14b - Switching Loss Waveform

Package Outline 1 - JEDEC Outline TO-220AB **Section D - page D-12**

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